



## **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> max         | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|-------------------|---------------------------------|----------------------------------------------|
| -30V              | 90mΩ @ V <sub>GS</sub> = -10V   | -3.8A                                        |
|                   | 134mΩ @ V <sub>GS</sub> = -4.5V | -3.1A                                        |

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Top View

- General Purpose Interfacing Switch
- Power Management Functions
- Load Switch for Portable Devices

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram

Top View

- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208e3
- Weight: 0.08 grams (Approximate)

Internal Schematic

# Ordering Information (Note 4)

| p      |                                             |                                                     |                           |
|--------|---------------------------------------------|-----------------------------------------------------|---------------------------|
|        | Part Number                                 | Case                                                | Packaging                 |
|        | DMG2307L-7                                  | SOT23                                               | 3,000/Tape & Reel         |
| Notes: | 1. No purposely added lead. Fully EU Direct | ive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/8 | 63/EU (RoHS 3) compliant. |

Drain

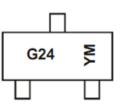
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



 $\begin{array}{l} G24 = \mbox{Product Type Marking Code} \\ \mbox{YM} &= \mbox{Date Code Marking} \\ \mbox{Y or } \overrightarrow{Y} &= \mbox{Year (ex: F = 2018)} \\ \mbox{M} &= \mbox{Month (ex: 9 = September)} \end{array}$ 

| Date | Code | Kev  |
|------|------|------|
| Date | COUE | 1/0/ |

| Year  | 2018 | 2019 | 2020 | 2021 | 202 | 2 20 | 23 2 | 024 | 2025 | 2026 | 2027 | 2028 |
|-------|------|------|------|------|-----|------|------|-----|------|------|------|------|
| Code  | F    | G    | Н    |      | J   |      | <    | L   | М    | Ν    | 0    | Р    |
| Month | Jan  | Feb  | Mar  | Apr  | Мау | Jun  | Jul  | Aug | Sep  | Oct  | Nov  | Dec  |
| Code  | 1    | 2    | 3    | 4    | 5   | 6    | 7    | 8   | 9    | 0    | Ν    | D    |



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                     |                 | Symbol                                           | Value            | Unit         |   |
|----------------------------------------------------|-----------------|--------------------------------------------------|------------------|--------------|---|
| Drain-Source Voltage                               |                 | V <sub>DSS</sub>                                 | -30              | V            |   |
| Gate-Source Voltage                                |                 |                                                  | V <sub>GSS</sub> | ±20          | V |
| Continuous Drain Current (Note 5) $V_{GS}$ = -10V  | Steady<br>State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | ID               | -2.5<br>-2.0 | А |
| Continuous Drain Current (Note 6) $V_{GS}$ = -10V  | Steady<br>State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | Ι <sub>D</sub>   | -3.8<br>-3.0 | A |
| Continuous Drain Current (Note 6) $V_{GS}$ = -10V  | t ≦10sec        | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | ID               | -4.6<br>-3.6 | A |
| Continuous Drain Current (Note 6) $V_{GS}$ = -4.5V | Steady<br>State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | Ι <sub>D</sub>   | -3.1<br>-2.5 | А |
| Pulsed Drain Current (Note 6)                      |                 | I <sub>DM</sub>                                  | -20              | А            |   |

# **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                                  | Symbol           | Value       | Unit |
|-----------------------------------------------------------------|------------------|-------------|------|
| Total Power Dissipation (Note 5)                                | Po               | 0.76        | W    |
| Thermal Resistance, Junction to Ambient (Note 5)                | R <sub>0JA</sub> | 159         | °C/W |
| Total Power Dissipation (Note 6)                                | PD               | 1.36        | W    |
| Thermal Resistance, Junction to Ambient (Note 6)                | Reja             | 94          | °C/W |
| Total Power Dissipation (Note 6) $t \leq 10 \text{sec}$         | PD               | 1.9         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) t $\leq$ 10sec | Reja             | 65.8        | °C/W |
| Operating and Storage Temperature Range                         | TJ, TSTG         | -55 to +150 | °C   |

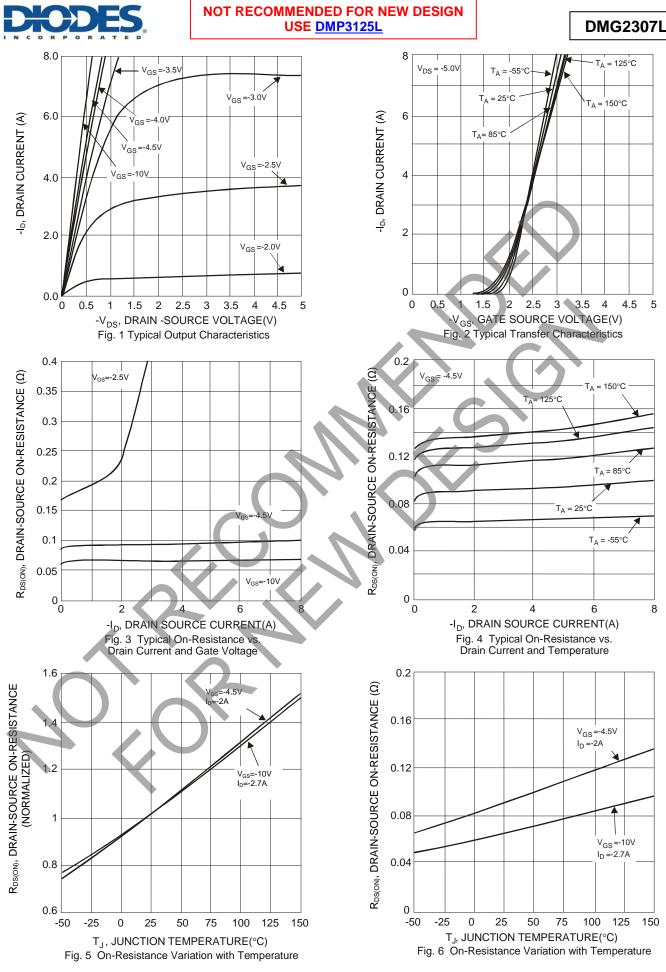
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                         | Symbol              | Min      | Тур   | Max   | Unit  | Test Condition                                                     |
|--------------------------------------------------------|---------------------|----------|-------|-------|-------|--------------------------------------------------------------------|
| OFF CHARACTERISTICS (Note 7)                           | Symbol              | I WILL   | тур   | IVIAX | Unit  | Test condition                                                     |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | -30      |       |       | V     | $V_{GS} = 0V, I_{D} = -250\mu A$                                   |
| Zero Gate Voltage Drain Current $@T_{C} = +25^{\circ}$ |                     |          |       | -1.0  | μA    | $V_{DS} = -30V, V_{GS} = 0V$                                       |
| Gate-Source Leakage                                    | Igss                | <u> </u> |       | ±100  | nA    | $V_{GS} = \pm 20V, V_{DS} = 0V$                                    |
| ON CHARACTERISTICS (Note 7)                            | 1 000               |          |       |       |       |                                                                    |
| Gate Threshold Voltage                                 | VGS(TH)             | -1.0     |       | -3.0  | V     | $V_{DS} = V_{GS}, I_D = -250 \mu A$                                |
| Static Drain-Source On-Resistance                      |                     | _        | 70    | 90    | mΩ    | $V_{GS} = -10V, I_D = -2.5A$                                       |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | _        | 105   | 134   | 11122 | $V_{GS} = -4.5V, I_D = -2.5A$                                      |
| Forward Transfer Admittance                            | Y <sub>fs</sub>     |          | 4.8   |       | S     | $V_{DS} = -10V, I_D = -2.5A$                                       |
| Diode Forward Voltage (Note 6)                         | V <sub>SD</sub>     |          | -0.75 | -1.0  | V     | $V_{GS} = 0V, I_{S} = -1A$                                         |
| DYNAMIC CHARACTERISTICS (Note 8)                       |                     |          |       |       |       |                                                                    |
| Input Capacitance                                      | C <sub>iss</sub>    |          | 371.3 |       | pF    |                                                                    |
| Output Capacitance                                     | C <sub>oss</sub>    | _        | 51.3  | —     | pF    | V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz        |
| Reverse Transfer Capacitance                           | Crss                | —        | 45.9  | _     | pF    |                                                                    |
| Gate Resistance                                        | Rg                  | _        | 17    |       | Ω     | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$                             |
| Total Gate Charge (V <sub>GS</sub> = -4.5V)            | Qg                  |          | 4.0   |       | nC    |                                                                    |
| Total Gate Charge (V <sub>GS</sub> = -10V)             | Qg                  | _        | 8.2   |       | nC    | $V_{GS} = -10V, V_{DS} = -15V,$                                    |
| Gate-Source Charge                                     | Qgs                 |          | 0.9   |       | nC    | I <sub>D</sub> = -3A                                               |
| Gate-Drain Charge                                      | Q <sub>gd</sub>     |          | 1.2   |       | nC    |                                                                    |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  |          | 4.8   |       | ns    |                                                                    |
| Turn-On Rise Time                                      | t <sub>R</sub>      |          | 7.3   | _     | ns    | $V_{DS} = -15V, V_{GS} = -10V,$                                    |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> |          | 22.4  |       | ns    | R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω,<br>I <sub>D</sub> = -1A |
| Turn-Off Fall Time                                     | t <sub>F</sub>      |          | 13.4  |       | ns    |                                                                    |

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.

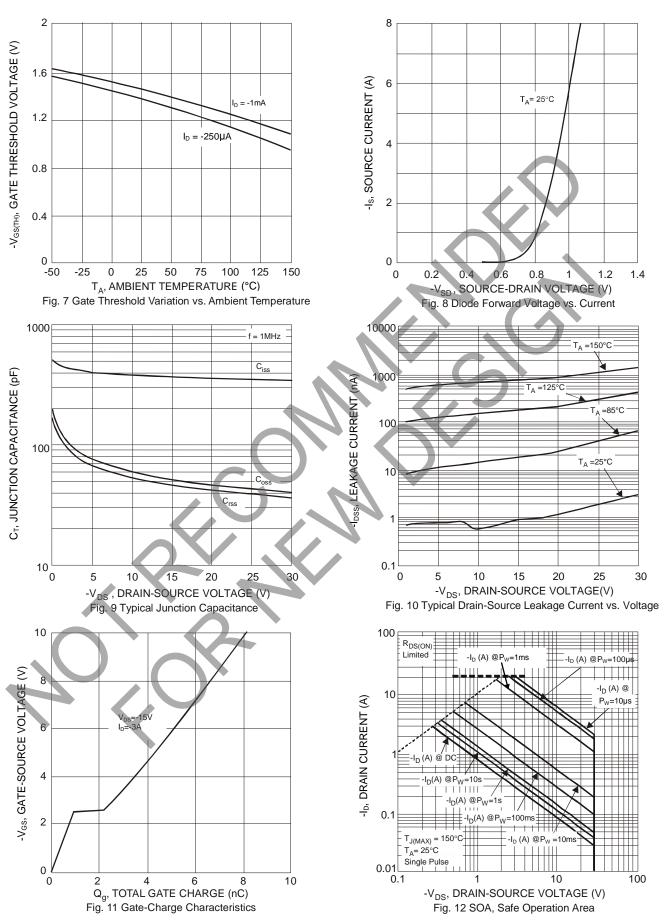
8. Guaranteed by design. Not subject to product testing.





### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3125L</u>

DMG2307L

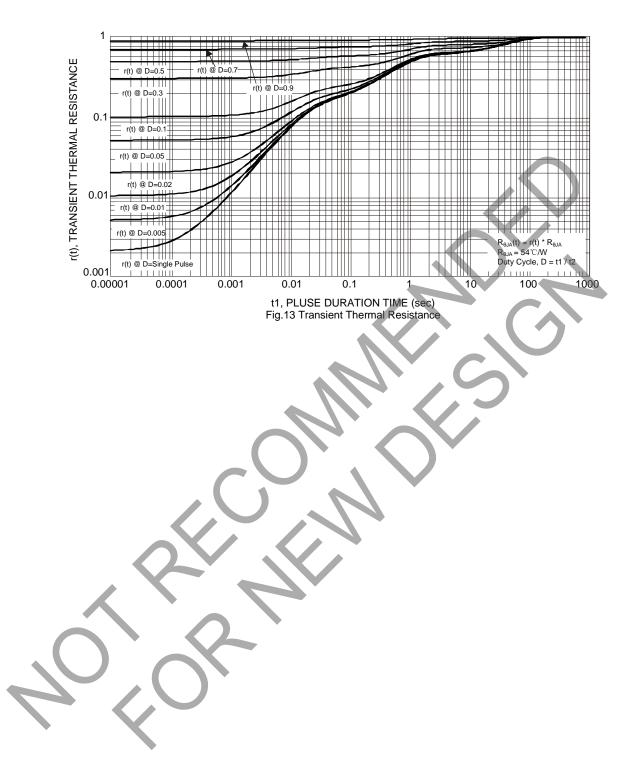


DMG2307L Document number: DS35415 Rev. 5 - 3



### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3125L</u>

DMG2307L

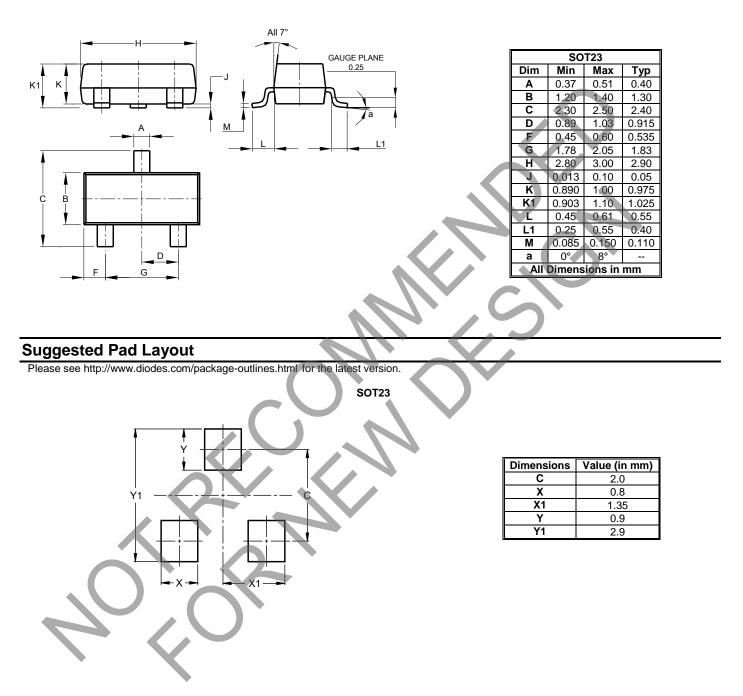




### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23





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